Number	Hit	s Search Text	DB	Time stamp
189	1	6 257/666.ccls. and electrodeposition	110775	
		did electiodeposition	USPAT;	2004/04/15
			US-PGPUB;	
			EPO; JPO;	
*			DERWENT;	
190	. 1	2 /257/000	IBM TDB	0.
			USPAT;	2004/04/15
		and (@ad<20010418)	US-PGPUB;	21:46
1 2	***		EPO; JPO;	21.40
			DERWENT;	
191	3:	leadless and electrodeposition	IBM_TDB	
			USPAT;	2004/04/15
			US-PGPUB;	21:32
	* * * * * * * * * * * * * * * * * * * *		EPO; JPO;	4
· ·			DERWENT;	
192			IBM TDB	· ·
192	24		USPAT;	12004/04/15
		(@ad<20010418)		2004/04/15
1			US-PGPUB;	21:29
1.			EPO; JPO;	
1.	1		DERWENT;	·   · · · · · · · · · · · · · · · · · ·
193	7	438/15: 6010 0-333	IBM_TDB	
	1 /	438/15:ccls. and electrodeposition	USPAT;	2004/04/15
1			US-PGPUB;	21:33
			EPO; JPO;	121.33
1	4. 3.		DEDMENTE:	1
			DERWENT;	
194	9	438/64 ccls. and electrodeposition	. IBM_TDB	
		and electrodeposition	USPAT;	2004/04/15
			US-PGPUB;	21:34
1 '	'], '		EPO; JPO;	1
			DERWENT;	
1.05	1		IBM TDB	
195	0	438/25.ccls. and electrodeposition	TON_TON	
			USPĀT;	2004/04/15
	1		US-PGPUB;	21:34
£ 15			EPO; JPO;	
	1	[1] [18] [18] [18] [18] [18] [18] [18] [	DERWENT;	
196		120/100	IBM TDB	.15
	8	438/123.ccls. and electrodeposition	USPAT;	2004/04/15
1000			US-PGPUB;	2004/04/15
	do.		EDO: TOO	21:43
			EPO; JPO;	* -
			DERWENT;	1
197	1 1	("3783499").PN.	IBM_TDB	
		( \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	USPAT	2004/04/15
198		420/204		21:38
1.	]	438/124.ccls. and electrodeposition	USPAT;	
M 4 /			US-PGPUB;	2004/04/15
'	±.			21:50
			EPO; JPO;	
*			DERWENT;	
199	2	438/55 ccls and alastical	IBM_TDB	1
- 3		438/55.ccls. and electrodeposition	USPAT;	2004/04/15
			US-PGPUB;	21:44
3 4 5			EPO; JPO;	
			DERWENT;	
200	. 2	438/51.ccls. and electrodeposition	IBM_TDB	
		orederodeposition	USPAT;	2004/04/15
	* 1		US-PGPUB;	21:45
			EPO; JPO;	
			DERWENT;	
201	1100		IBM TDB	
	1466	(leadframe or (lead adj frame)) and	USPAT;	2004/04/25
	•	(electrodeposition or bath)		2004/04/15
			US-PGPUB;	21:46
· · ·		* * *	EPO; JPO;	- · ·
			DERWENT;	; <u> </u>
202	1440	(//)	IBM TDB	·
	1440	((leadframe or (lead adj frame)) and	USPAT;	2004/04/15
1 E.		(electrodeposition or bath) ) and (loads		2004/04/15
	f	or lead)	US-PGPUB;	21:46
			EPO; JPO;	* -
·			DERWENT;	
			DERWENT; IBM TDB	*

203	'	"L2020" and (@ad<20010418)	IICDAM.	10004/04/
		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2004/04/15
	1.		US-PGPUB;	21:46
	1		EPO; JPO;	
			DERWENT;	
204	1440	1//1	IBM TDB	
	1440		USPAT;	2004/04/15
	1	(electrodeposition or bath) ) and (loads	US-PGPUB,	21:46
		or lead)) and (leads or lead).	EPO; JPO;	21:46
			EPO, SPO;	
			DERWENT;	•
205	1131	(((leadframe or (lead adj frame)) and	IBM_TDB	
,	1	(electrodenosition and	USPAT;	2004/04/15
	İ	(electrodeposition or bath) ) and (leads	US-PGPUB;	21:47
	7	or lead)) and (@ad<20010418)	EPO; JPO;	
	* 0		DERWENT;	
06			IBM TDB	
06	45	((((leadframe or (lead adj frame)) and	TDM IDD	
4,41		(electrodeposition or bath) and (leads	USPAT;	2004/04/15
		or lead)) and (@ad<20010418)) and	US-PGPUB;	21:47
		leadless (edd(20010418)) and	EPO; JPO;	1
			DERWENT;	
	370	ologened	IBM TDB	
	. 570	electrodeposition same frame	USPAT;	2004/04/15
			US-PGPUB;	18:31
			EPO; JPO;	10:31
A 7 1			EPO, JPO;	
			DERWENT;	
	309	(electrodeposition same frame) and	IBM_TDB	-
		(Cad<20010418)	USPAT;	2004/04/15
		(044,20010410)	US-PGPUB;	21:25
* 0			EPO; JPO;	
			DERWENT;	
			IBM TDB	•
* 1	97	((electrodeposition same frame) and		
		(@ad<20010418)) and (chip or die or ic or	'USPAT;	2004/04/15
음화		semiconductor)	US-PGPUB;	21:24
	- 00		EPO; JPO;	
			DERWENT;	*
<del> </del>	<del></del>		IBM TDB	